

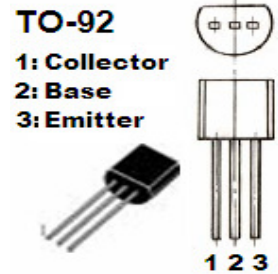


Features:

- High Current transistor

Maximum Rating (TA=25°C unless otherwise note)

Parameter	Symbol	Value	Units
Collector-Base Voltage	BC546	80	V
	BC547	50	
	BC548	30	
Collector-Emitter Voltage	BC546	65	V
	BC547	45	
	BC548	30	
Emitter-Base Voltage	V_{EB0}	6	V
Collector Current –Continuous	I_C	100	mA
Collector Power Dissipation	P_D	625	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55-150	°C



Electrical Characteristics (T_{amb}=25°C unless otherwise specified):

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{CBO}	I _C =100μA, I _E =0	BC546	80		V
			BC547	50		
			BC548	30		
Collector-emitter breakdown voltage	V _{CEO}	I _C =1mA, I _B =0	BC546	65		V
			BC547	45		
			BC548	30		
Emitter-base breakdown voltage	V _{CBO}	I _E =10μA, I _C =0		6		V
Collector cut-off current	I _{CBO}	V _{CB} = 70 V, I _E =0	BC546		0.1	μA
		V _{CB} = 50 V, I _E =0	BC547			
		V _{CB} = 30 V, I _E =0	BC548			
Collector cut-off current	I _{EBO}	V _{CE} = 60 V, I _B =0	BC546		0.1	μA
		V _{CE} = 45 V, I _B =0	BC547			
		V _{CE} = 30 V, I _B =0	BC548			
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0	BC546		0.1	μA
			BC547			
			BC548			
DC current gain	h _{FE}	V _{CE} =5V, I _C = 2mA	BC546	110	800	
			BC547	110	800	
			BC548	110	800	
		BC546A/BC547A/BC548A	110	220		
		BC546B/BC547B/BC548B	220	450		
BC557C/BC547C/BC548C	420	800				
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =5mA			0.3	V
Base-emitter voltage	V _{BE(sat)}	I _C =100mA, I _B =5mA			1.1	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f= 100 MHz		150		MHz